

NPN SILICON TRIPLE DIFFUSED TRANSISTOR

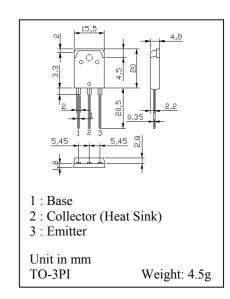
...designed for power amplifier applications.

FEATURE:

- High Collector Breakdown Voltage: VcEo= 180V (Min.)
- Complementary to PMA1516
- Recommend for 80W High Fiderity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a = 25 \, ^{\circ}C$)

Symbol	Value	Unit
Vсво	180	>
VCEO	180	>
VEBO	5	V
Ic	12	Α
Ів	1.2	Α
Pc	130	W
Tj	150	°C
Tstg	-55 ~ 150	°C
	VCBO VCEO VEBO IC IB PC Tj	VCBO 180 VCEO 180 VEBO 5 IC 12 IB 1.2 PC 130 Tj 150



ELECTRICAL CHARACTERISTICS ($T_a = 25 \, ^{\circ}C$)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector Cutoff Current	Ісво	VcB= 180V, IE=0	-	-	5	μΑ
Emitter Cutoff Current	ІЕВО	VEB=5V, IC=0	-	-	5	μА
Collector Emitter Breakdown	V(BR)CEO	Ic=50mA, IB=0	180	-	-	V
Voltage						
DC Current Gain	hFE(1)	Vce=5V, Ic=1A	55	-	180	-
	hFE(2)	Vce=5V, Ic=7A	35	70	-	-
Collector Emitter Saturation	VCE(sat)	IC=8A, IB=0.8A	-	0.3	2	V
Voltage						
Base Emitter Voltage	VBE	Vce=5V, Ic=7A	-	1	1.5	V
Transition Frequency	fτ	Vce=5V, Ie=1A	-	30	ı	MHz
Collector Output Capacitance	Cob	Vcb=10V, IE=0, f=1MHz	-	270	1	pF

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Classification of hFE(1)

Class	R	0		
hFE(1)	55 to 110	90 to 180		

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